# **General Purpose Transistors**

## **PNP Silicon**

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	-60	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ic	-600	mAdc
Collector Current – Peak (Note 3)	I <sub>CM</sub>	-1200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation – FR–5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation – Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Total Device Dissipation – Heat Spreader or equivalent, (Note 4) @T <sub>A</sub> = 25°C	P <sub>D</sub>	350	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

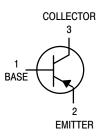
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.
- 3. Reference SOA curve.
- 4. Heat Spreader or equivalent = 450 mm<sup>2</sup>, 2 oz.



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SOT-23 (TO-236AB) CASE 318 STYLE 6

#### **MARKING DIAGRAM**



2F = Device Code M = Date Code\* • = Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

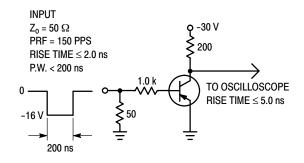
Device	Package	Shipping <sup>†</sup>
MMBT2907ALT1G	SOT-23	3000 / Tape &
SMMBT2907ALT1G	(Pb-Free)	Reel
MMBT2907ALT3G	SOT-23	10,000 / Tape &
SMMBT2907ALT3G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Charac	teristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		·		-L	1
Collector-Emitter Breakdown Voltage (No $(I_C = -1.0 \text{ mAdc}, I_B = 0)$ $(I_C = -10 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	-60 -60	- -	Vdc	
Collector – Base Breakdown Voltage (I <sub>C</sub> :	= -10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-60	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = -	-10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = −30 Vdc,	$V_{EB(off)} = -0.5 \text{ Vdc}$	I <sub>CEX</sub>	-	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$		I <sub>CBO</sub>	- -	-0.010 -10	μAdc
Base Cutoff Current (V <sub>CE</sub> = -30 Vdc, V <sub>EI</sub>	$B_{\text{Off}} = -0.5 \text{ Vdc}$	I <sub>BL</sub>	-	-50	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C = -0.1 \text{ mAdc},  V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -1.0 \text{ mAdc},  V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -10 \text{ mAdc},  V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -150 \text{ mAdc},  V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -500 \text{ mAdc},  V_{CE} = -10 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	75 100 100 100 50	- - 300 -	-	
Collector – Emitter Saturation Voltage (Not $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ (Not $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$	V <sub>CE(sat)</sub>		-0.4 -1.6	Vdc	
Base – Emitter Saturation Voltage (Note $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$	V <sub>BE(sat)</sub>	- -	-1.3 -2.6	Vdc	
SMALL-SIGNAL CHARACTERISTICS				•	•
Current – Gain – Bandwidth Product (Not (I <sub>C</sub> = –50 mAdc, V <sub>CE</sub> = –20 Vdc, f = 10	f <sub>T</sub>	200	_	MHz	
Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> :	C <sub>obo</sub>	-	8.0	pF	
Input Capacitance (V <sub>EB</sub> = −2.0 Vdc, I <sub>C</sub> =	C <sub>ibo</sub>	_	30		
SWITCHING CHARACTERISTICS					
Turn-On Time		t <sub>on</sub>	ı	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t <sub>d</sub>	_	10	
Rise Time	,	t <sub>r</sub>	_	40	no
Turn-Off Time		t <sub>off</sub>	-	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$	t <sub>s</sub>	_	80	
Fall Time	.61 – .62 – .0 (00)	t <sub>f</sub>	-	30	

- 5. Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .
- 6.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.





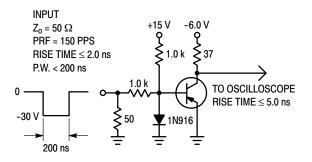


Figure 2. Storage and Fall Time Test Circuit

#### **TYPICAL CHARACTERISTICS**

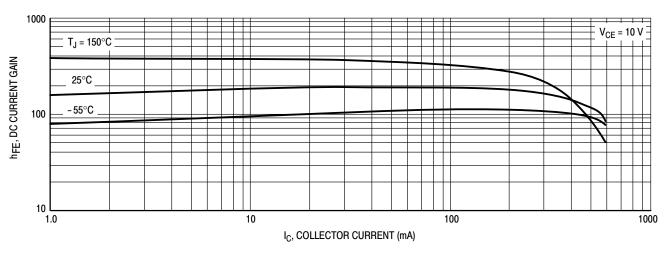


Figure 3. DC Current Gain

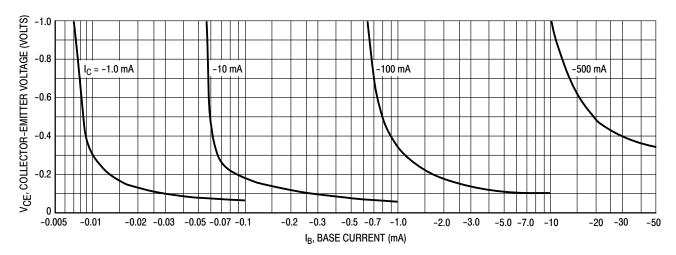


Figure 4. Collector Saturation Region

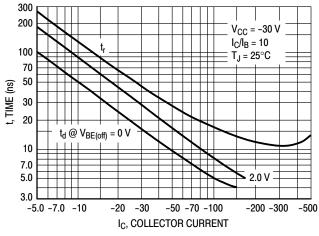


Figure 5. Turn-On Time

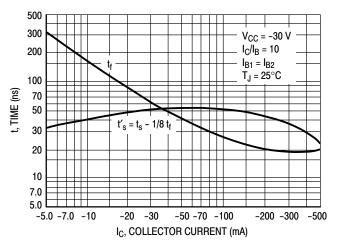
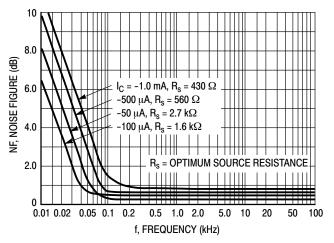


Figure 6. Turn-Off Time

# TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

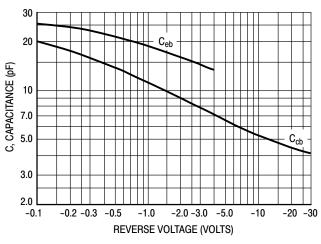
 $V_{CE}$  = 10 Vdc,  $T_A$  = 25°C



8.0 NF, NOISE FIGURE (dB) 6.0  $I_C = -50 \mu A$ -100 μA -500 μA 4.0 1.0 mA 2.0 100 200 2.0 k 50 k **5**0 1.0 k 5.0 k 10 k 20 k R<sub>s</sub>, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



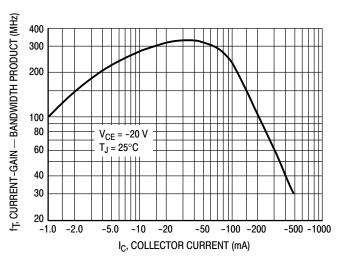
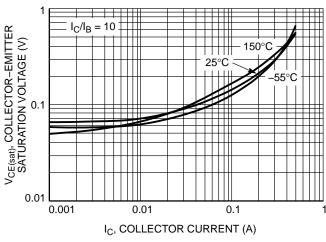


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



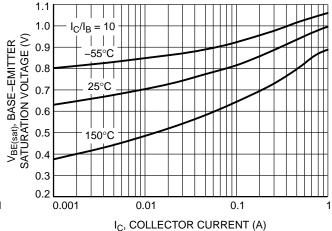
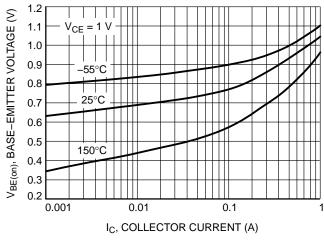


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Saturation Voltage vs.
Collector Current

# TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

 $V_{CE}$  = 10 Vdc,  $T_A$  = 25°C



+0.5

0

R<sub>0</sub>VC for V<sub>CE(sat)</sub>

-1.5

-2.0

R<sub>0</sub>VB for V<sub>BE</sub>

-2.5

-0.1 -0.2 -0.5 -1.0 -2.0 -5.0 -10 -20 -500

I<sub>C</sub>, COLLECTOR CURRENT (mA)

Figure 13. Base Emitter Voltage vs. Collector Current

Figure 14. Temperature Coefficients

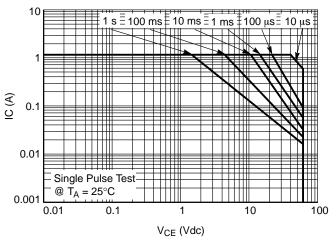


Figure 15. Safe Operating Area



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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